

## L-Band Radar Transistor

The high power pulsed radar transistor device part number IB1214M130 is designed for L-Band radar systems operating over the instantaneous bandwidth of 1.210-1.400 GHz. While operating in class C mode this common base device supplies a minimum of 130 watts of peak pulse power under the conditions of 330µs pulse width and 10% duty cycle, at Pin=20W. All devices are 100% screened for large signal RF parameters.



### Silicon Bipolar

- Ultra-high  $f_T$

### Class C Operation

- High Efficiency

### Common Base Configuration

- Single Power Supply

### Gold Metal

- Maximum Reliability

### Emitter Ballasting

- Optimum Thermal Distribution

### Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

### Be0 Package

- Unmatched Thermal Reliability

### RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed

*TYPICAL DATA    TYPICAL DATA    TYPICAL DATA    TYPICAL DATA*

General Information	Test Sequence	Freq	Pin	RL	POUT	GP	dG	IC	nc	Droop	VSWR-S	VSWR-LMT
IB1214M130	Name	(MHz)	(W)	(dB)	(W)	(dB)	(dB)	(A)	(%)	(dB)	2:1 (P-F)	3:1 (P-F)
Date:	4/10/2009											
Assbly Lot - SN :	D2494-1	Nominal	1210	20.0 -15.0	161.0	9.06		5.170	62.3	0.05	P	P
Wafer :	NA											
Test Fixture :	1303-1092	Nominal	1300	20.0 -15.0	162.0	9.08	0.28	5.800	55.9	0.03	P	P
Pass / Fail :	Device Passes											
OPERATOR:	FB	Nominal	1400	20.0 -18.0	152.0	8.81		5.660	53.7	0.03	P	P
Pulse: 330us-10%	Vcc=50V											

**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	$V_{CES}$	--	75	V	$V_{BE}=0V$ .
BD	Emitter-Base Voltage	$V_{EBO}$	--	2	V	--
BD	Storage Temperature Range	$T_{STG}$	-55	+150	°C	--
BD	Operating Junction Temperature Range	$T_J$	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

**THERMAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.433	°C/W	$V_{CC}=50V$ , Pulse Format=330us, 10%, $T_F=25\pm 5^\circ C$ , $P_{in}=20W$ , $P_{OUT}=130W$ , $N_C=50\%$
Note	Screen 'BD' = parameter qualified By Design.					

**PROCESSING SPECIFICATIONS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification.
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071.6, Test Condition C.
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

**DC ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	$BV_{CES}$	75	--	V	$I_C=20mA$ , $V_{BE}=0V$ , $T_F=25\pm 5^\circ C$ .
100%	Zero Base Voltage Collector Leakage Current	$I_{CES}$	--	200	$\mu A$	$V_{CE}=50V$ , $V_{BE}=0V$ , $T_F=25\pm 5^\circ C$ .
100%	DC Current Gain	$H_{FE}$	20	150	--	$V_{CE}=5V$ , $I_C=0.2A$ , $T_F=25\pm 5^\circ C$ .

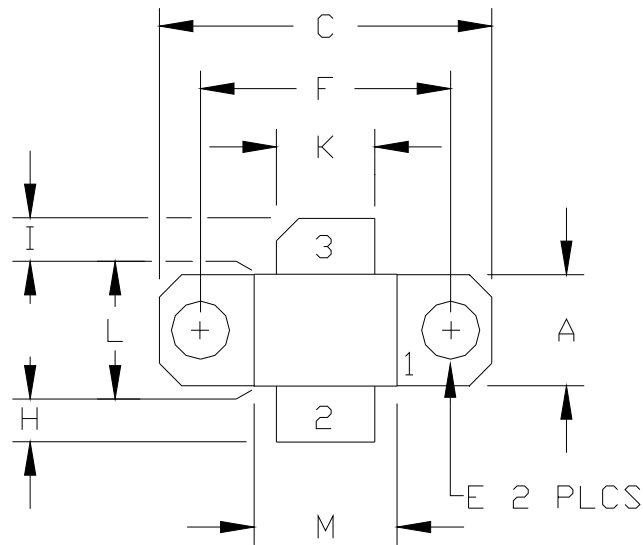
**RF ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	RL	-18	-10	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Output Power	$P_{OUT}$	130	260	W	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Power Gain	Gp	8.15	11.15	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Collector Efficiency ( $P_O/I_C/V_{CC}$ )	$N_C$	50	75	%	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Pulse Amplitude Droop	Droop	-0.5	0.5	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
100%	Gain Flatness	dG	0	1	dB	Calculate from Gain at each frequency F.
100%	Stability into 2:1 VSWR	VSWR-S	--	--	--	2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	3:1 Load Mismatch Tolerance	VSWR-LMT	--	--	--	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$ Rotate 3:1 output VSWR through 360° phase. Post test $P_O$ = Pre test $P_O \pm 10W$ .
BD	Pulse Risetime	RT	--	80	ns	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN1}, P_{IN2}, P_{IN3}, F=F1, F2, F3.$
Note	V1 = 50V; PW1 = 330 $\mu$ s; DF1 = 10%; $P_{IN1} = P_{IN2} = P_{IN3} = 20W$ ; F1 = 1.210 GHz, F2 = 1.300 GHz, F3 = 1.400 GHz.					
Note	$T_F$ = Device flange temperature.					
Note	Screen 'BD' = parameter qualified By Design.					

**BROADBAND RF TEST FIXTURE IMPEDANCE CHARACTERISTICS**

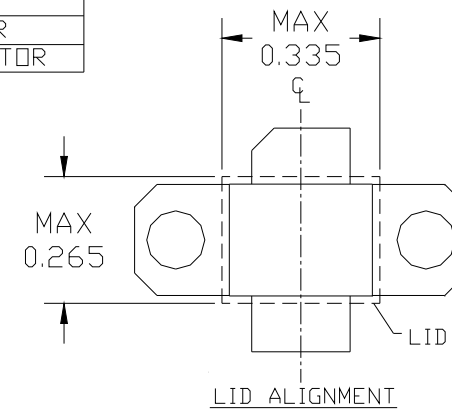
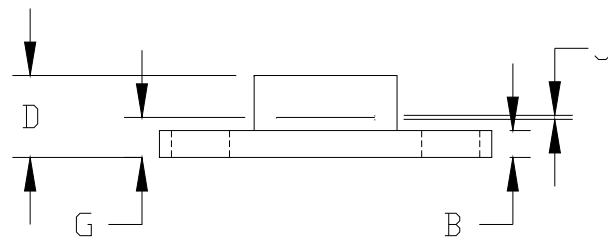
Frequency (MHz)	$Z_{IF}$ ( $\Omega$ )	$Z_{OF}$ ( $\Omega$ )
1.210	2.19-j1.74	5.12+j3.07
1.300	2.29-j1.04	4.84-j2
1.400	2.59-j0.37	4.79-j0.92
Impedance Definition		

**PACKAGE DIMENSIONAL OUTLINE DRAWING**

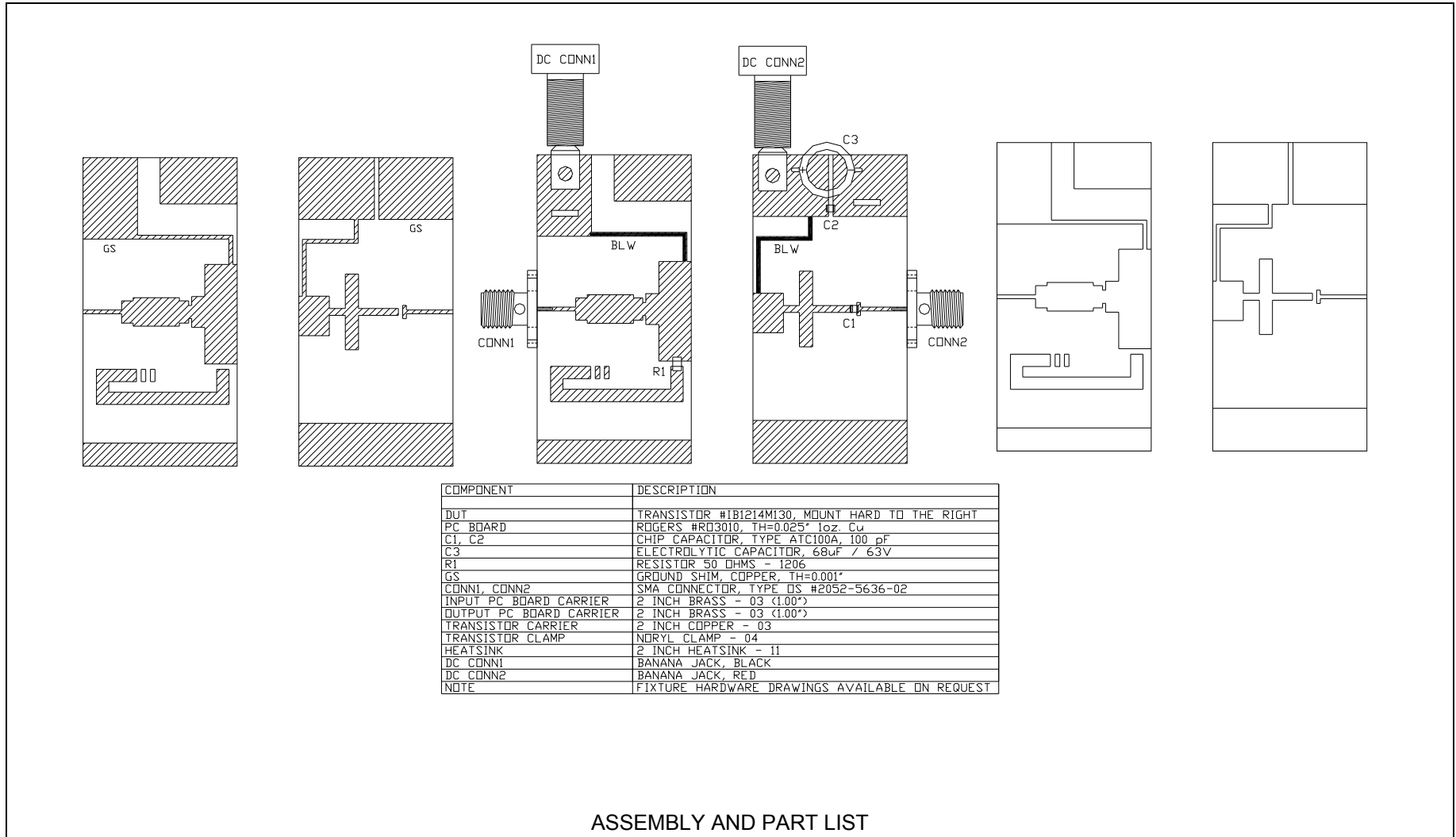


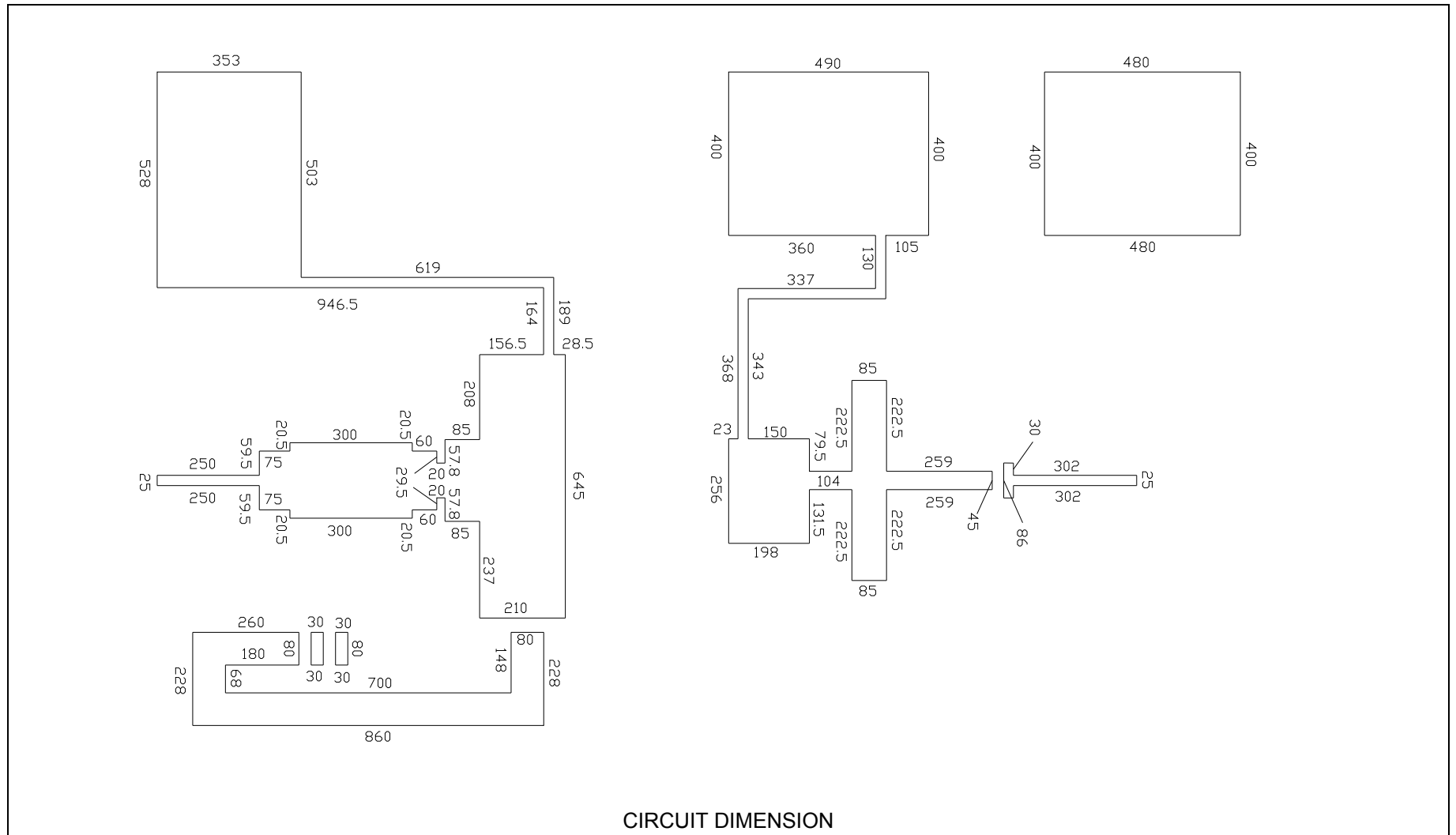
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.243	0.253	6.17	6.43
B	0.055	0.065	1.40	1.65
C	0.739	0.749	18.77	19.02
D	0.165	0.185	4.19	4.70
E	0.125	0.135	3.18	3.43
F	0.555	0.565	14.10	14.35
G	0.082	0.092	2.08	2.34
H	0.070	0.125	1.78	3.18
I	0.070	0.125	1.78	3.18
J	0.004	0.006	0.10	0.15
K	0.215	0.225	5.46	5.72
L	0.245	0.255	6.22	6.48
M	0.315	0.325	8.00	8.26

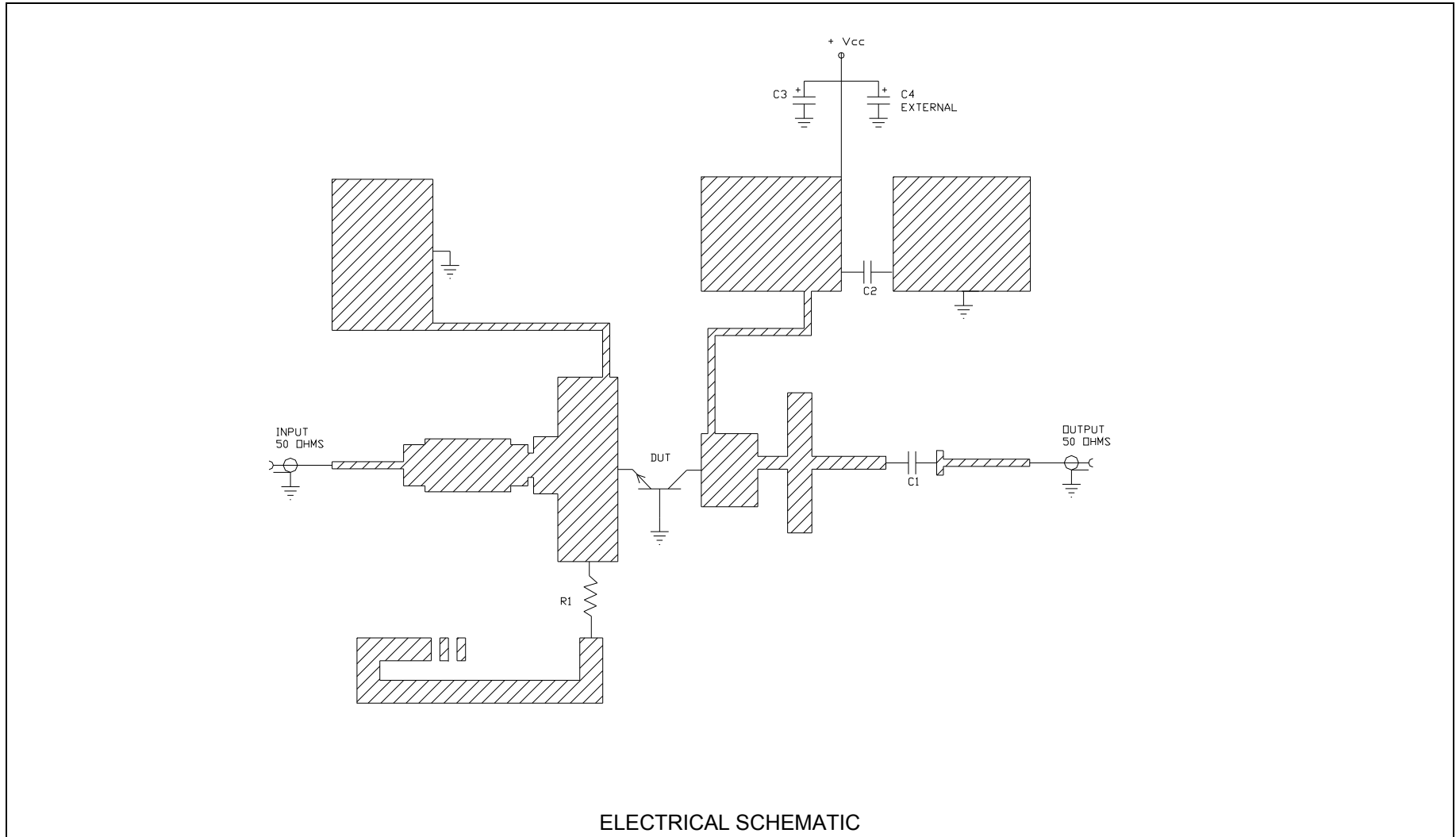
PIN SCHEDULE	
1	BASE
2	EMITTER
3	COLLECTOR



**RF TEST FIXTURE**







**DEFINITIONS**

<b>Data Sheet Status</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>Maximum Ratings</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

**WARNING**

<b>Product and environmental safety - toxic materials</b>
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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